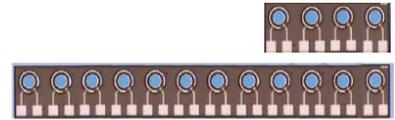




PDAx-85A2G 2.5Gbps GaAs PIN Photodiode Chip Array

Overview

The Lasermate PDAx-85A2G is 2.5/3.125Gbps, low dark current and low capacitance, GaAs photodiode chip array available with up to 12 channels. PDAx-85A2G is designed for use in fiber optic data communication applications.



Features

- Two top-side wire bond pads per channel
- AR coated for 850nm
- Package: 1x4 chips, 1x12 chips
- Data rate 2.5/3.125Gbps per channel
- Low dark current and low capacitance
- Uniform characteristics

Applications

- High speed Data communications
- Gigabit ethernet
- Fiber channel

Product Overview

The following table lists the available part numbers, as well as the package type of each of the part numbers.

Part Number	Package
PDA4-85A2G	1x4 Array
PDA12-85A2G	1x12 Array

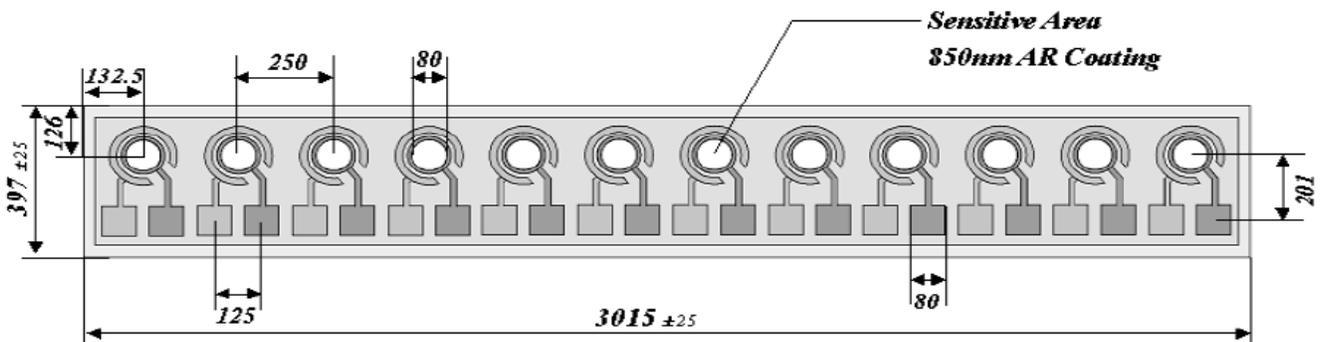
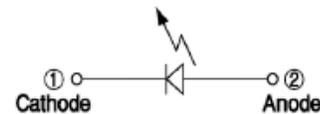
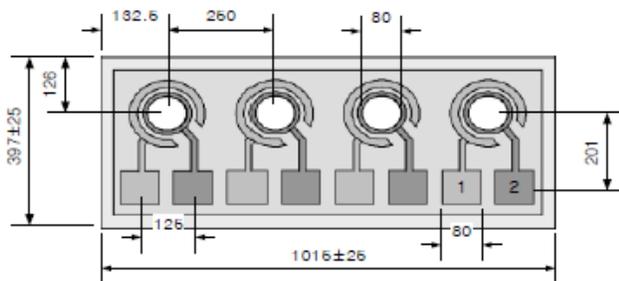
Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage Temperature	-40	100	°C	
Operating Temperature	0	85	°C	
Forward Current		10	mA	
Reverse Voltage		40	V	

Electro-Optical Characteristics (T _a =25°C unless otherwise stated)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Sensitive Area	D		80		um	In diameter
Responsivity	R	0.5	0.6		A/W	V _R =1.6V, λ=850nm
Dark Current	I _D		0.1	1.0	nA	V _R =1.6V
Breakdown Voltage	V _B	40			V	I _F =1uA
Capacitance	C		0.4	0.5	pF	V _R =1.6V, f=1MHz
Peak Wavelength	λ		850		nm	
Rise and Fall Times	t _r /t _f		100/100		ps	V _R =1.6V, 20%~80%
Bandwidth	f _{-3dB}		5.0		GHz	V _R =1.6V

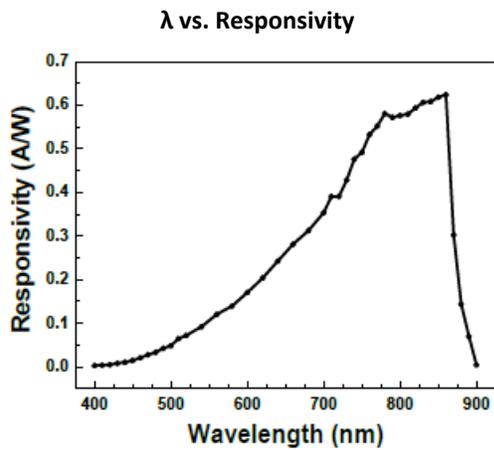
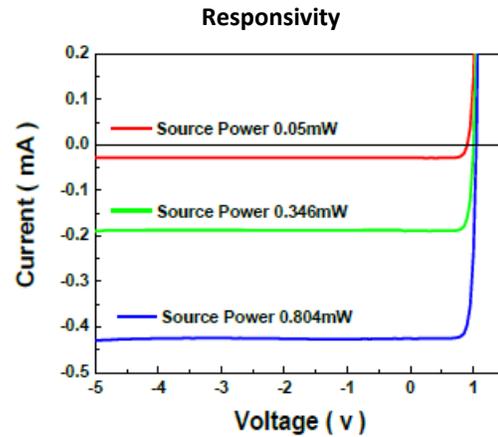
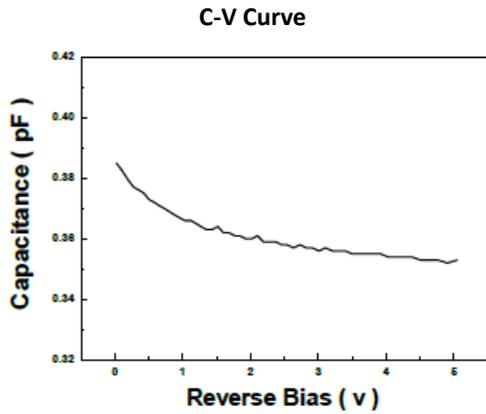
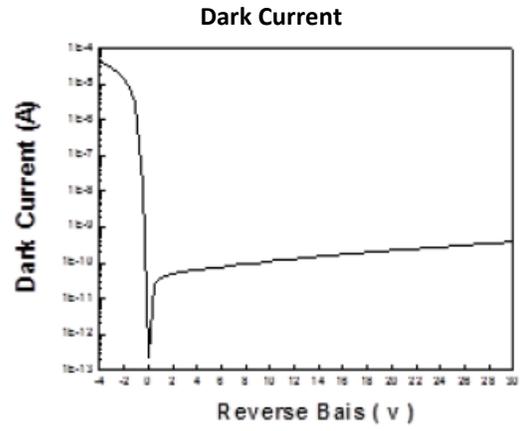
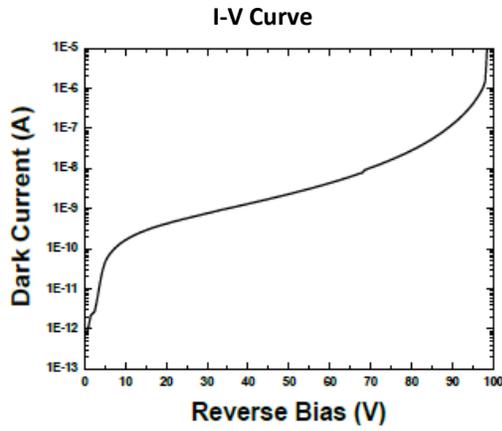
Outline Dimensions (unit: um)

Die Height: 200±15 um





Typical Characteristics



Note: Specifications are subject to change without notice.